

On concentration-dependent microhardness in semiconductor solid solutions

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[en] Consideration is being given to the effect of interaction of static deformation fields, formed by impurity atoms, on mechanical properties of crystals and on microhardness H -correlated integral characteristic of plastic strain resistance under contact compression - in particular. Anomalies, corresponding to passing from dissolved to concentrated solid solutions, were revealed on curves of concentration dependence of microhardness of solid solutions on the base of semiconductor A⁴B⁶ compounds

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